VS-HFA16PA120C-N3

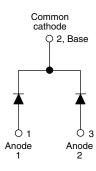
Vishay Semiconductors

HEXFRED[®] Ultrafast Soft Recovery Diode, 2 x 8 A



www.vishay.com





PRIMARY CHARACTERISTICS								
I _{F(AV)}	2 x 8 A							
V _R	1200 V							
V _F at I _F	2.4 V							
t _{rr} typ.	28 ns							
T _J max.	150 °C							
Package	TO-247AC 3L							
Circuit configuration	Common cathode							

FEATURES

- Ultrafast and ultrasoft recovery
- Very low I_{RRM} and Q_{rr}
- \bullet Designed and qualified according to ${\sf JEDEC}^{\circledast}{\sf -}{\sf JESD}$ 47
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

BENEFITS

- Reduced RFI and EMI
- · Reduced power loss in diode and switching transistor
- Higher frequency operation
- Reduced snubbing
- Reduced parts count

DESCRIPTION

VS-HFA16PA120C... is a state of the art ultrafast recovery diode. Employing the latest in epitaxial construction and advanced processing techniques it features a superb combination of characteristics which result in performance which is unsurpassed by any rectifier previously available. With basic ratings of 1200 V and 8 A per leg continuous current, the VS-HFA16PA120C... is especially well suited for use as the companion diode for IGBTs and MOSFETs. In addition to ultrafast recovery time, the HEXFRED® product line features extremely low values of peak recovery current (I_{RRM}) and does not exhibit any tendency to "snap-off" during the t_b portion of recovery. The HEXFRED features combine to offer designers a rectifier with lower noise and significantly lower switching losses in both the diode and the switching transistor. These HEXFRED advantages can help to significantly reduce snubbing, component count and heatsink sizes. The HEXFRED VS-HFA16PA120C... is ideally suited for applications in power supplies and power conversion systems (such as inverters), motor drives, and many other similar applications where high speed, high efficiency is needed.

ABSOLUTE MAXIMUM RATINGS									
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS					
Cathode to anode voltage	V _R		1200	V					
Maximum continuous forward current	I_	T _C = 100 °C	8						
per device	- I _F	$1_{\rm C} = 100$ C	16	А					
Single pulse forward current	I _{FSM}	t _p = 10 ms	130	A					
Maximum repetitive forward current	I _{FRM}		32						
Maximum power dissipation	PD	T _C = 25 °C	73.5	W					
	ΓD	T _C = 100 °C	29	vv					
Operating junction and storage temperature range	T _J , T _{Stg}		-55 to +150	°C					

Revision: 11-Oct-2019

1

Document Number: 94055

For technical questions within your region: <u>DiodesAmericas@vishay.com</u>, <u>DiodesAsia@vishay.com</u>, <u>DiodesEurope@vishay.com</u> THIS DOCUMENT IS SUBJECT TO CHANGE WITHOUT NOTICE. THE PRODUCTS DESCRIBED HEREIN AND THIS DOCUMENT ARE SUBJECT TO SPECIFIC DISCLAIMERS, SET FORTH AT <u>www.vishay.com/doc?91000</u>



RoHS COMPLIANT HALOGEN FREE www.vishay.com

SHAY

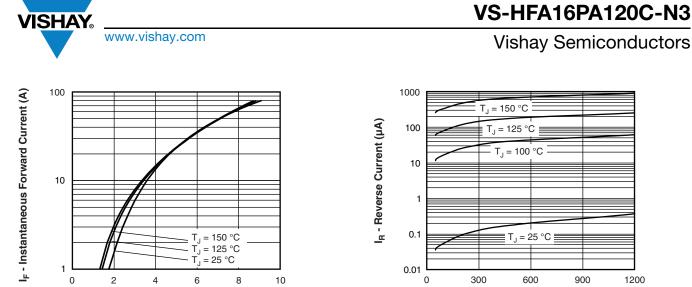
Vishay Semiconductors

ELECTRICAL SPECIFICATIONS PER LEG ($T_J = 25 \text{ °C}$ unless otherwise specified)									
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS			
Cathode to anode breakdown voltage	V _{BR}	I _R = 100 μA	1200	-	-				
Maximum forward voltage	V _{FM}	I _F = 8.0 A	-	2.6	3.3	V			
		I _F = 16 A	-	3.4	4.3				
		I _F = 8.0 A, T _J = 125 °C	-	2.4	3.1				
Maximum reverse		$V_{R} = V_{R}$ rated	-	0.31	10				
leakage current	I _{RM}	$T_J = 125 \text{ °C}, V_R = 0.8 \text{ x } V_R \text{ rated}$	-	135	1000	μA			
Junction capacitance	CT	V _R = 200 V	-	11	20	pF			
Series inductance	Ls	Measured lead to lead 5 mm from package	-	8.0	-	nH			

DYNAMIC RECOVERY CHARACTERISTICS PER LEG (T_J = 25 °C unless otherwise specified)									
PARAMETER	SYMBOL	TEST CO	NDITIONS	MIN.	TYP.	MAX.	UNITS		
Reverse recovery time	t _{rr}	$I_F = 1.0 \text{ A}, \text{ d}_F/\text{d}t = 200$) A/µs, V _R = 30 V	-	28	-			
	t _{rr1}	T _J = 25 °C		-	63	95	ns		
	t _{rr2}	T _J = 125 °C		-	106	160			
Peak recovery current	I _{RRM1}	T _J = 25 °C	l _F = 8.0 A dl⊧/dt = 200 A/µs	-	4.5	8.0	A		
	I _{RRM2}	T _J = 125 °C		-	6.2	11			
	Q _{rr1}	T _J = 25 °C	$V_{\rm R} = 200 \text{V}$	-	140	380			
Reverse recovery charge	Q _{rr2}	T _J = 125 °C		-	335	880	no		
Peak rate of recovery current	dl _{(rec)M} /dt1	T _J = 25 °C		-	133	-	A/µs		
during t _b	dl _{(rec)M} /dt2	T _J = 125 °C		-	85	-			

THERMAL - MECHANICAL SPECIFICATIONS										
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS				
Lead temperature	T _{lead}	0.063" from case (1.6 mm) for 10 s	-	-	300	°C				
Thermal resistance, junction to case	R _{thJC}		-	-	1.7					
Thermal resistance, junction to ambient	R _{thJA}	Typical socket mount	-	-	40	K/W				
Thermal resistance, case to heatsink	R _{thCS}	Mounting surface, flat, smooth, and greased	-	0.25	-					
Weight			-	6.0	-	g				
weight			-	0.21	-	oz.				
Mounting torque			6.0 (5.0)	-	12 (10)	kgf · cm (lbf · in)				
Marking device		Case style TO-247AC 3L	HFA16PA120C							

Document Number: 94055



V_{FM} - Forward Voltage Drop (V)

Fig. 1 - Maximum Forward Voltage Drop Characteristics

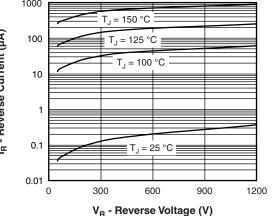


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage

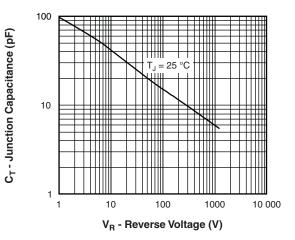


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

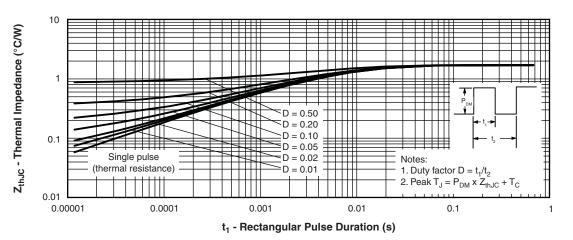


Fig. 4 - Maximum Thermal Impedance ZthJC Characteristics

Revision: 11-Oct-2019 3 For technical questions within your region: DiodesAmericas@vishay.com, DiodesAsia@vishay.com, DiodesEurope@vishay.com THIS DOCUMENT IS SUBJECT TO CHANGE WITHOUT NOTICE. THE PRODUCTS DESCRIBED HEREIN AND THIS DOCUMENT ARE SUBJECT TO SPECIFIC DISCLAIMERS, SET FORTH AT www.vishay.com/doc?91000



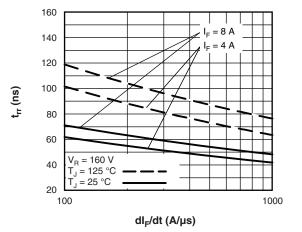


Fig. 5 - Typical Reverse Recovery Time vs. dl_F/dt

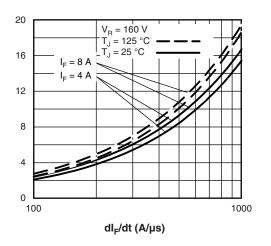
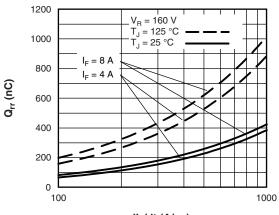


Fig. 6 - Typical Recovery Current vs. dl_F/dt







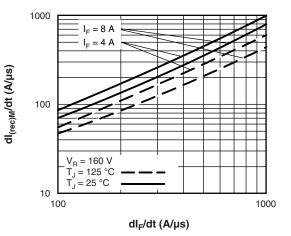


Fig. 8 - Typical $dI_{(rec)M}/dt$ vs. dI_F/dt

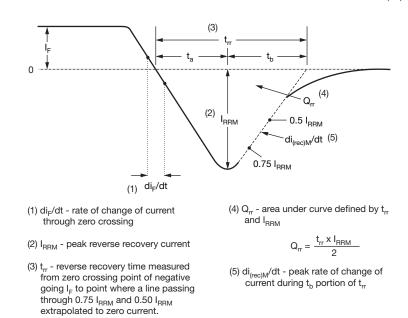


Fig. 9 - Reverse Recovery Waveform and Definitions

Revision: 11-Oct-2019	4	Document Number: 94055
For technical questions within your region:	: DiodesAmericas@vishay.com, DiodesAsia@vis	hay.com, DiodesEurope@vishay.com
	E WITHOUT NOTICE. THE PRODUCTS DESCR	

I_{rr} (A)

VS-HFA16PA120C-N3

Vishay Semiconductors

Vishay Semiconductors



ORDERING INFORMATION TABLE

Device code	VS-	HF	Α	16	PA	120	С	-N3
		2	3	4	5	6	7	8
	1 - 2 - 3 - 4 - 5 - 6 - 7 -	HEX Elec Cur PA Volt	KFRED [®] ctron irra rent rati = TO-2 ⁴ cage rati		= 16 A) pins) = 1200			
	7 -	Env	ironmer	n catho ntal digit en-free,	:	complia	int, and	totally

ORDERING INFORMATION (Example)									
PREFERRED P/N	QUANTITY PER T/R	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION						
VS-HFA16PA120C-N3	25	500	Antistatic plastic tube						

LINKS TO RELATED DOCUMENTS						
Dimensions	www.vishay.com/doc?96138					
Part marking information	www.vishay.com/doc?95007					



Vishay Semiconductors

TO-247AC 3L

DIMENSIONS in millimeters and inches



SYMBOL	MILLIMETERS		INC	HES	NOTES	SYMBOL	MILLIN	IETERS	INC	HES	NOTES
STWIDOL	MIN.	MAX.	MIN.	MAX.	NOTES	STWDOL	MIN.	MAX.	MIN.	MAX.	NOTES
A	4.65	5.31	0.183	0.209		D2	0.51	1.35	0.020	0.053	
A1	2.21	2.59	0.087	0.102		E	15.29	15.87	0.602	0.625	3
A2	1.17	1.37	0.046	0.054		E1	13.46	-	0.53	-	
b	0.99	1.40	0.039	0.055		е	5.46	BSC	0.215	5 BSC	
b1	0.99	1.35	0.039	0.053		ØК	0.2	254	0.0)10	
b2	1.65	2.39	0.065	0.094		L	14.20	16.10	0.559	0.634	
b3	1.65	2.34	0.065	0.092		L1	3.71	4.29	0.146	0.169	
b4	2.59	3.43	0.102	0.135		ØΡ	3.56	3.66	0.14	0.144	
b5	2.59	3.38	0.102	0.133		Ø P1	-	7.39	-	0.291	
С	0.38	0.89	0.015	0.035		Q	5.31	5.69	0.209	0.224	
c1	0.38	0.84	0.015	0.033		R	4.52	5.49	0.178	0.216	
D	19.71	20.70	0.776	0.815	3	S	5.51	BSC	0.217	' BSC	
D1	13.08	-	0.515	-	4						

Notes

⁽¹⁾ Dimensioning and tolerancing per ASME Y14.5M-1994

(2) Contour of slot optional

(3) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body

(4) Thermal pad contour optional with dimensions D1 and E1

⁽⁵⁾ Lead finish uncontrolled in L1

⁽⁶⁾ Ø P to have a maximum draft angle of 1.5 to the top of the part with a maximum hole diameter of 3.91 mm (0.154")

⁽⁷⁾ Outline conforms to JEDEC[®] outline TO-247 with exception of dimension Q

Revision: 20-Jun-17

1



Vishay

Disclaimer

ALL PRODUCT, PRODUCT SPECIFICATIONS AND DATA ARE SUBJECT TO CHANGE WITHOUT NOTICE TO IMPROVE RELIABILITY, FUNCTION OR DESIGN OR OTHERWISE.

Vishay Intertechnology, Inc., its affiliates, agents, and employees, and all persons acting on its or their behalf (collectively, "Vishay"), disclaim any and all liability for any errors, inaccuracies or incompleteness contained in any datasheet or in any other disclosure relating to any product.

Vishay makes no warranty, representation or guarantee regarding the suitability of the products for any particular purpose or the continuing production of any product. To the maximum extent permitted by applicable law, Vishay disclaims (i) any and all liability arising out of the application or use of any product, (ii) any and all liability, including without limitation special, consequential or incidental damages, and (iii) any and all implied warranties, including warranties of fitness for particular purpose, non-infringement and merchantability.

Statements regarding the suitability of products for certain types of applications are based on Vishay's knowledge of typical requirements that are often placed on Vishay products in generic applications. Such statements are not binding statements about the suitability of products for a particular application. It is the customer's responsibility to validate that a particular product with the properties described in the product specification is suitable for use in a particular application. Parameters provided in datasheets and / or specifications may vary in different applications and performance may vary over time. All operating parameters, including typical parameters, must be validated for each customer application by the customer's technical experts. Product specifications do not expand or otherwise modify Vishay's terms and conditions of purchase, including but not limited to the warranty expressed therein.

Hyperlinks included in this datasheet may direct users to third-party websites. These links are provided as a convenience and for informational purposes only. Inclusion of these hyperlinks does not constitute an endorsement or an approval by Vishay of any of the products, services or opinions of the corporation, organization or individual associated with the third-party website. Vishay disclaims any and all liability and bears no responsibility for the accuracy, legality or content of the third-party website or for that of subsequent links.

Vishay products are not designed for use in life-saving or life-sustaining applications or any application in which the failure of the Vishay product could result in personal injury or death unless specifically qualified in writing by Vishay. Customers using or selling Vishay products not expressly indicated for use in such applications do so at their own risk. Please contact authorized Vishay personnel to obtain written terms and conditions regarding products designed for such applications.

No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted by this document or by any conduct of Vishay. Product names and markings noted herein may be trademarks of their respective owners.

© 2024 VISHAY INTERTECHNOLOGY, INC. ALL RIGHTS RESERVED

Revision: 01-Jul-2024